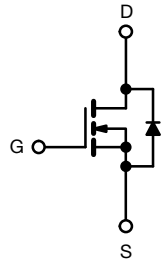
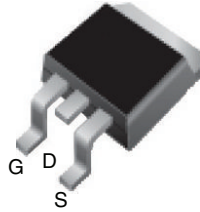


EF Series Power MOSFET With Fast Body Diode

D²PAK (TO-263)


N-Channel MOSFET

FEATURES

- 4th generation E series technology
- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low effective capacitance ($C_{o(er)}$)
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
 COMPLIANT
 HALOGEN
FREE

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Motor drives
 - Battery chargers
 - Solar (PV inverters)

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ typ. (Ω) at 25 °C	$V_{GS} = 10$ V	0.059
Q_g max. (nC)	77	
Q_{gs} (nC)	19	
Q_{gd} (nC)	16	
Configuration	Single	

ORDERING INFORMATION

Package	D ² PAK (TO-263)
Lead (Pb)-free and halogen-free	SiHB068N60EF-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)


PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	600	V	
Gate-source voltage	V_{GS}	± 30		
Continuous drain current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	41	A
		$T_C = 100$ °C	26	
Pulsed drain current ^a	I_{DM}	115		
Linear derating factor		2	W/°C	
Single pulse avalanche energy ^b	E_{AS}	226	mJ	
Maximum power dissipation	P_D	250	W	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C	
Drain-source voltage slope	dV/dt	$T_J = 125$ °C	70	V/ns
Reverse diode dV/dt ^d		50		
Soldering recommendations (peak temperature) ^c	For 10 s	260	°C	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 120$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 4$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, $di/dt = 210$ A/ μ s, starting $T_J = 25$ °C



THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Maximum junction-to-ambient	R _{thJA}	62	°C/W
Maximum junction-to-case (drain)	R _{thJC}	0.5	

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	600	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA	-	0.63	-	V/°C
Gate-source threshold voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	3	-	5	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = ± 30 V	-	-	± 1	μA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 480 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 480 V, V _{GS} = 0 V, T _J = 125 °C	-	-	2	mA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V I _D = 16 A	-	0.059	0.068	Ω
Forward transconductance	g _{fs}	V _{DS} = 30 V, I _D = 16 A	-	9	-	S
Dynamic						
Input capacitance	C _{iSS}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz	-	2628	-	pF
Output capacitance	C _{oss}		-	122	-	
Reverse transfer capacitance	C _{rSS}		-	7	-	
Effective output capacitance, energy related ^a	C _{o(er)}		-	87	-	
Effective output capacitance, time related ^b	C _{o(tr)}	V _{DS} = 0 V to 480 V, V _{GS} = 0 V	-	543	-	
Total gate charge	Q _g	V _{GS} = 10 V I _D = 16 A, V _{DS} = 480 V	-	51	77	nC
Gate-source charge	Q _{gs}		-	19	-	
Gate-drain charge	Q _{gd}		-	16	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 480 V, I _D = 16 A, V _{GS} = 10 V, R _g = 9.1 Ω	-	27	54	ns
Rise time	t _r		-	55	83	
Turn-off delay time	t _{d(off)}		-	53	80	
Fall time	t _f		-	35	70	
Gate input resistance	R _g		f = 1 MHz, open drain	0.3	0.7	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	41	A
Pulsed diode forward current	I _{SM}		-	-	115	
Diode forward voltage	V _{SD}	T _J = 25 °C, I _S = 16 A, V _{GS} = 0 V	-	-	1.2	V
Reverse recovery time	t _{rr}	T _J = 25 °C, I _F = I _S = 16 A, di/dt = 100 A/μs, V _R = 400 V	-	152	304	ns
Reverse recovery charge	Q _{rr}		-	1	2	μC
Reverse recovery current	I _{RRM}		-	14	-	A

Notes

- a. C_{oss(er)} is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
- b. C_{oss(tr)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

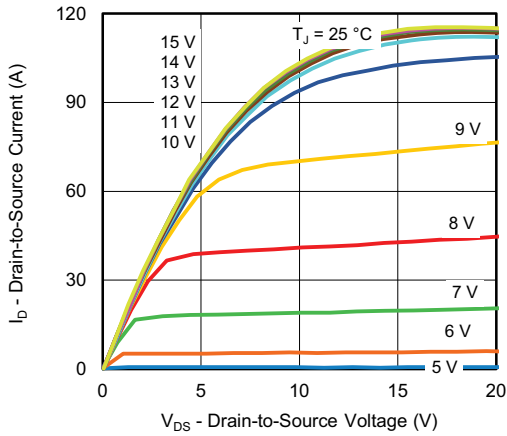


Fig. 1 - Typical Output Characteristics

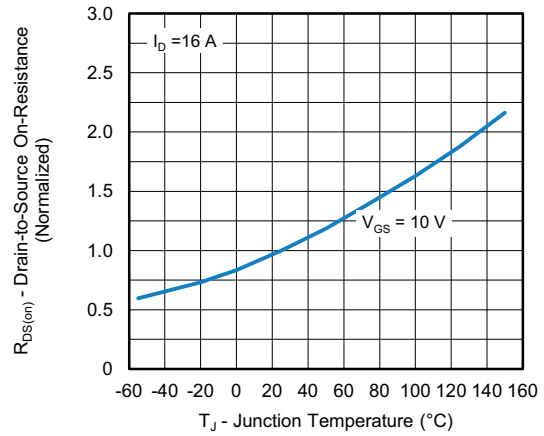


Fig. 4 - Normalized On-Resistance vs. Temperature

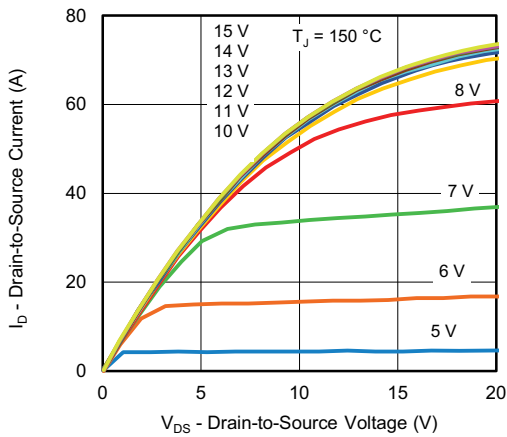


Fig. 2 - Typical Output Characteristics

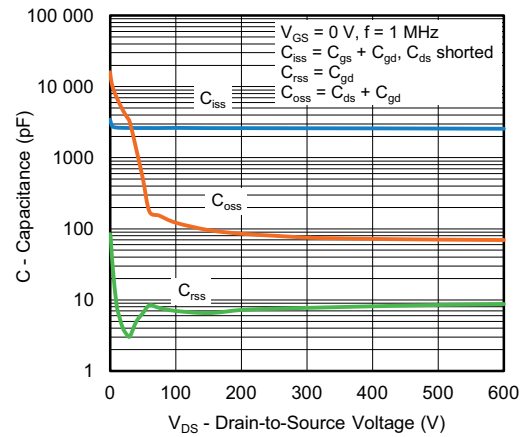


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

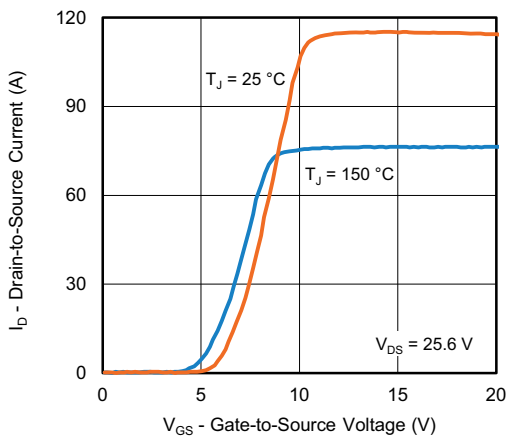


Fig. 3 - Typical Transfer Characteristics

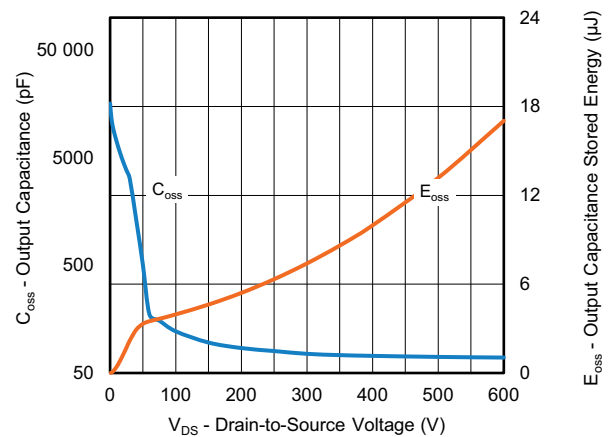


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

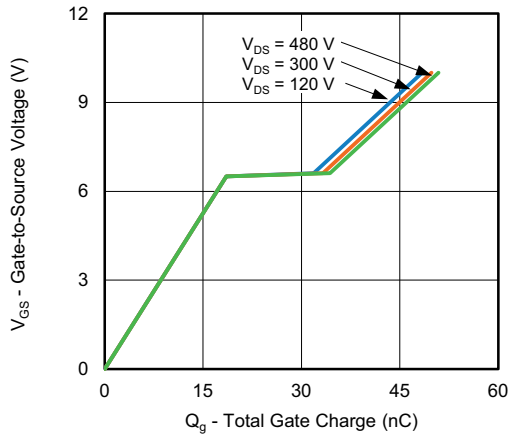


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

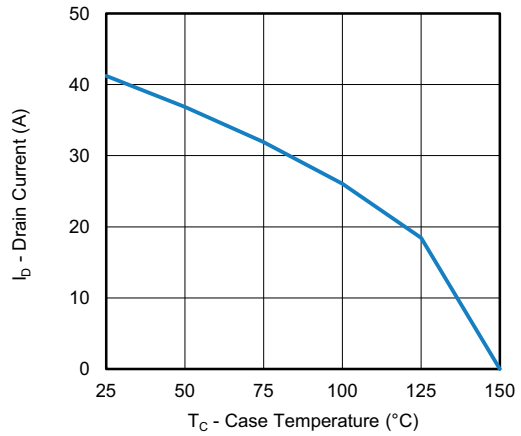


Fig. 10 - Maximum Drain Current vs. Case Temperature

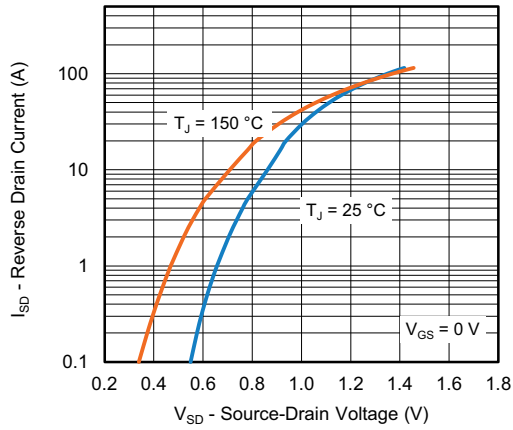


Fig. 8 - Typical Source-Drain Diode Forward Voltage

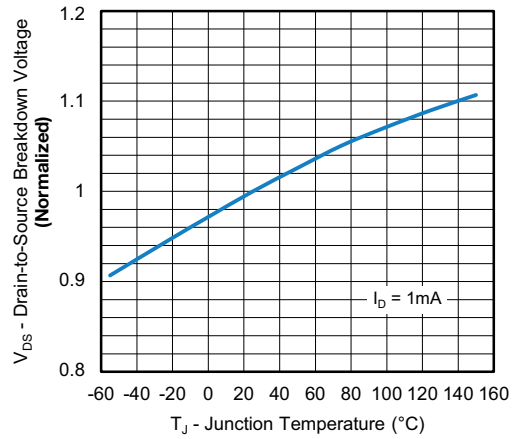


Fig. 11 - Temperature vs. Drain-to-Source Voltage

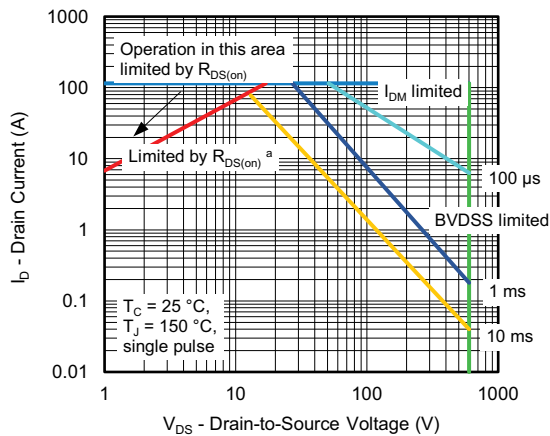


Fig. 9 - Maximum Safe Operating Area

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

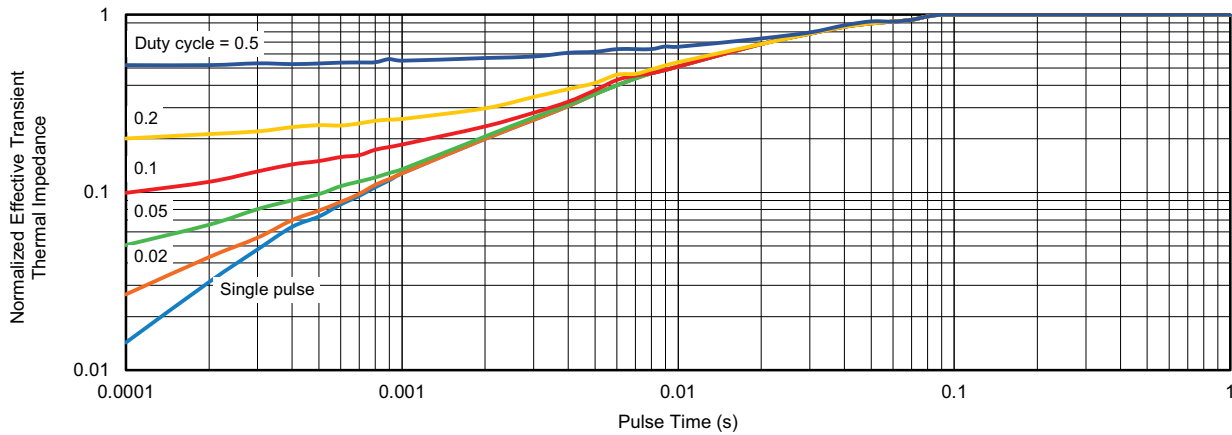


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

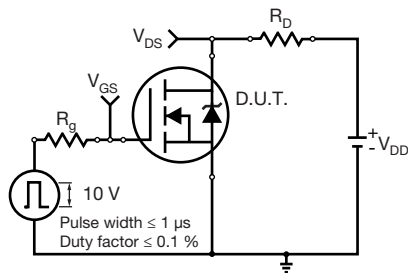


Fig. 13 - Switching Time Test Circuit

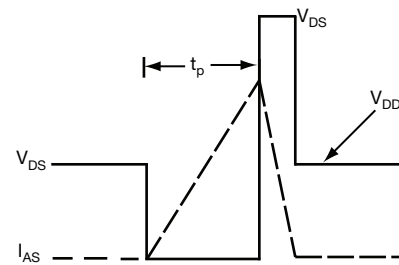


Fig. 16 - Unclamped Inductive Waveforms

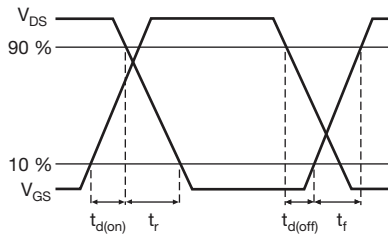


Fig. 14 - Switching Time Waveforms

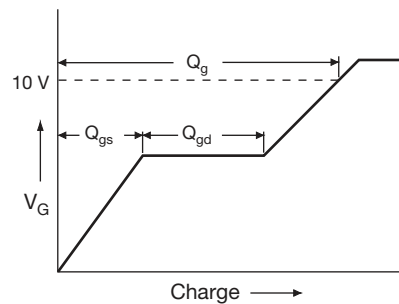


Fig. 17 - Basic Gate Charge Waveform

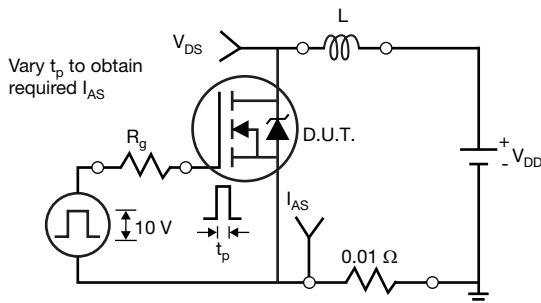


Fig. 15 - Unclamped Inductive Test Circuit

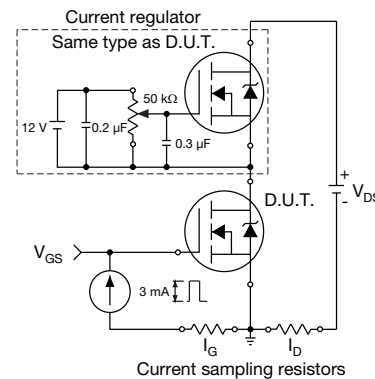
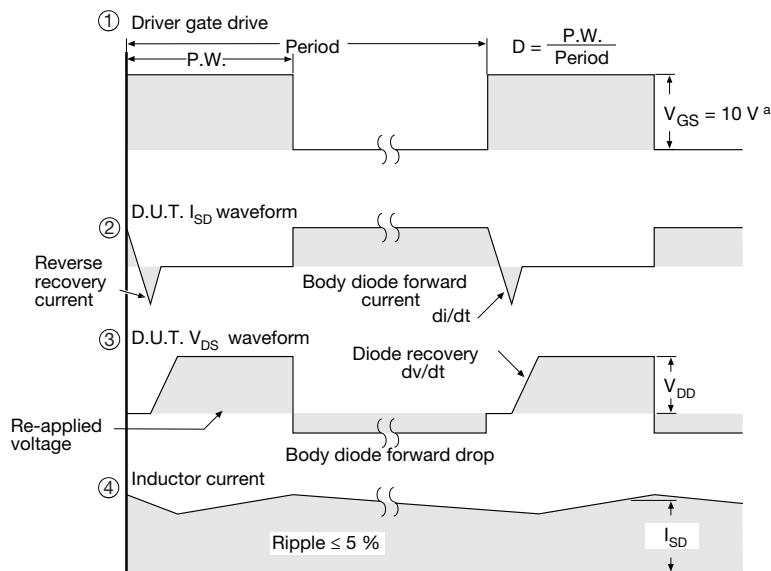
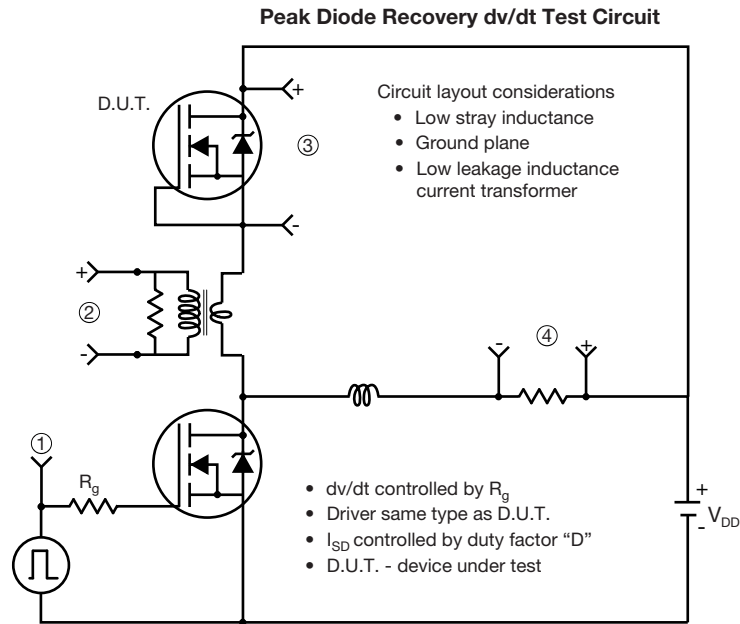


Fig. 18 - Gate Charge Test Circuit



Note
a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 19 - For N-Channel

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